TM12P10P

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

V_{DS} = -100 V I_D =-12A

$R_{DS(ON)}$= 170mΩ(typ.) @ V_{GS}=-10V

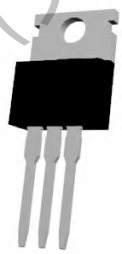
100% UIS Tested

100% R_g Tested

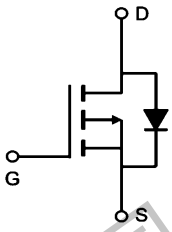
Green Product

P:TO-220AB

Marking: 12P10



G D S



Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Curren	-12	A
	Continuous Drain Current-T_C=100℃	-9.2	
I_{DM}	Pulsed Drain Current	-52	
P_D	Power Dissipation	40	W
E_{AS}	Single pulse avalanche energy	65	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristics

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	1.67	℃/W

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Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	-100	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=-100V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±10	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	-1	-2	-3	V
$R_{DS(ON)}$	Drain-Source On Resistance[2]	V_{GS}=-10V,I_D=16A	---	170	200	mΩ
		V_{GS}=-4.5V,I_D=A	---	---	---	
G_{FS}	Forward Transconductance	$V_{DS=}$.50V, I_D=-10A	12	---	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-25V, V_{GS}=0V, f=1MHz	---	760	---	pF
C_{oss}	Output Capacitance		---	260	---	
C_{rss}	Reverse Transfer Capacitance		---	170	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=-50V, I_D=10A, R_{GEN}=9.1Ω .V_{GS}=-10V	---	14	---	ns
t_r	Rise Time		---	18	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	50	---	ns
t_f	Fall Time		---	18	---	ns
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-50V, I_D=-10A	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	7	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage[2]	V_{GS}=0V,I_S=10A	---	---	-1.2	V
Is	Diode Forward Current (Note 2)	-	---	---	-12	A
Trr	Reverse Recovery Time	TJ = 25°C, IF =-10A di/dt = 100A/ s(Note3)	---	35	---	nS
Qrr	Reverse Recovery Charge		---	46	---	nC

Typical Characteristics

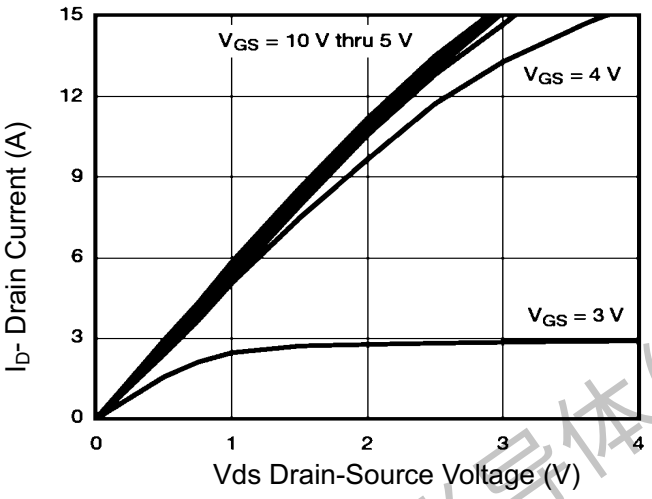


Figure 1 Output Characteristics

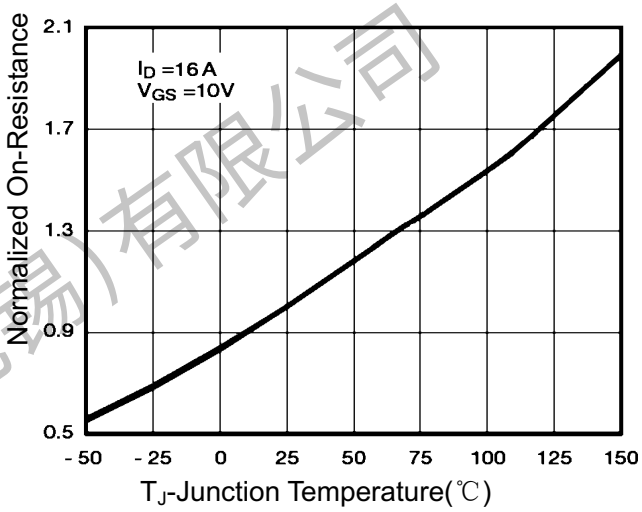


Figure 4 Rdson-JunctionTemperature

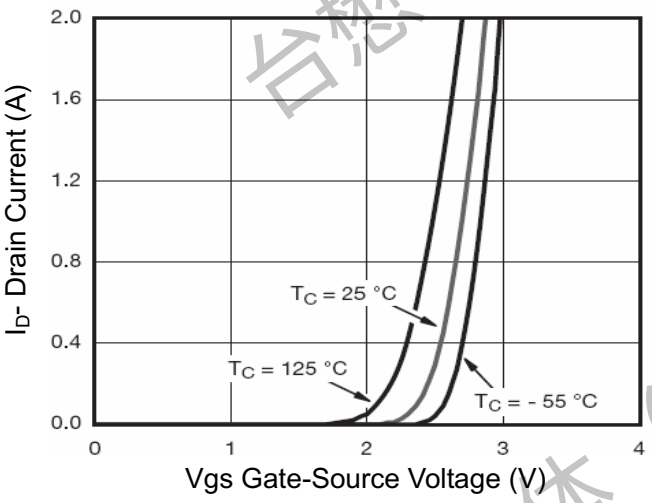


Figure 2 Transfer Characteristics

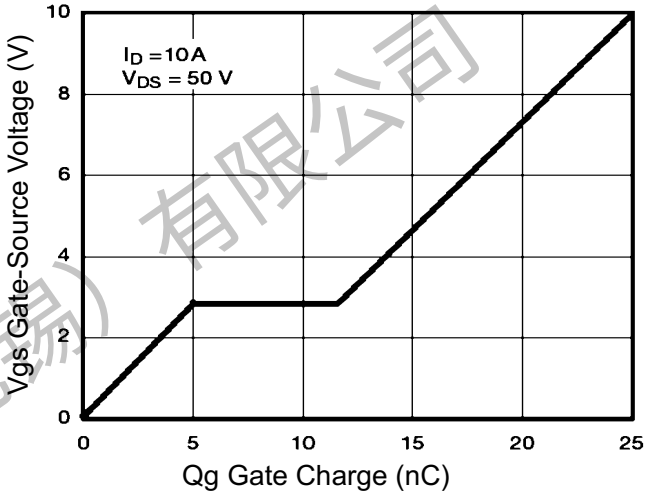


Figure 5 Gate Charge

TM12P10P

P-Channel Enhancement Mosfet

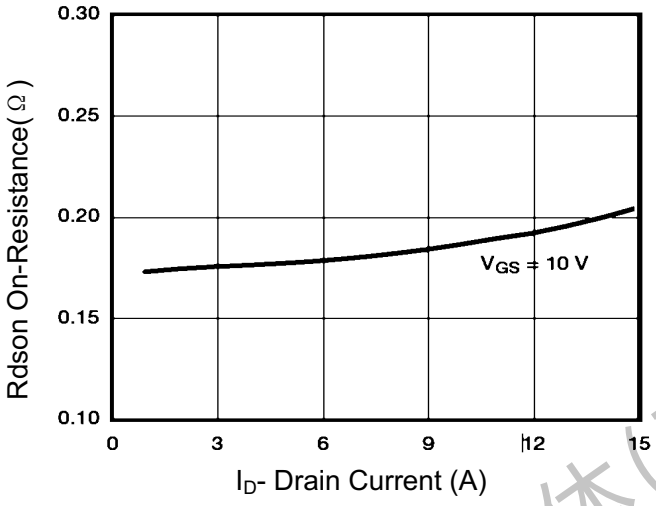


Figure 3 Rdson- Drain Current

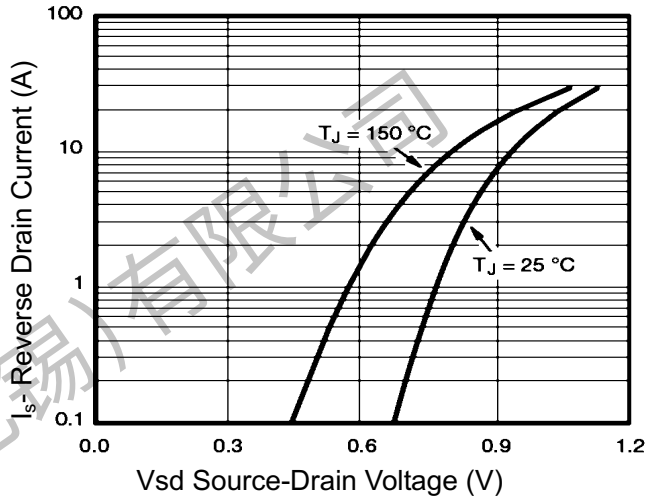


Figure 6 Source- Drain Diode Forward

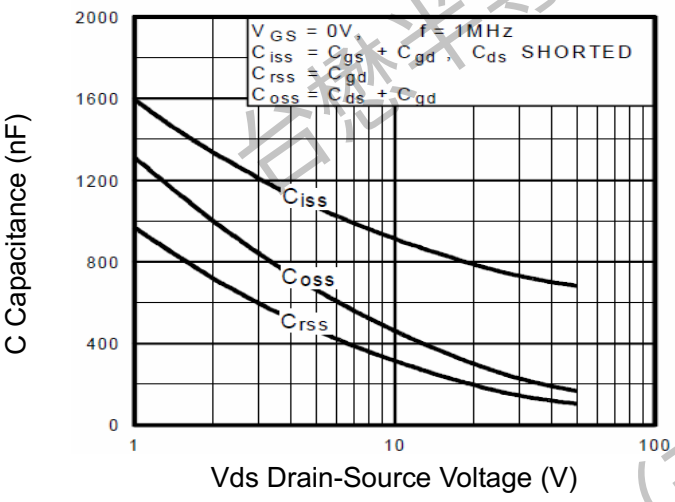
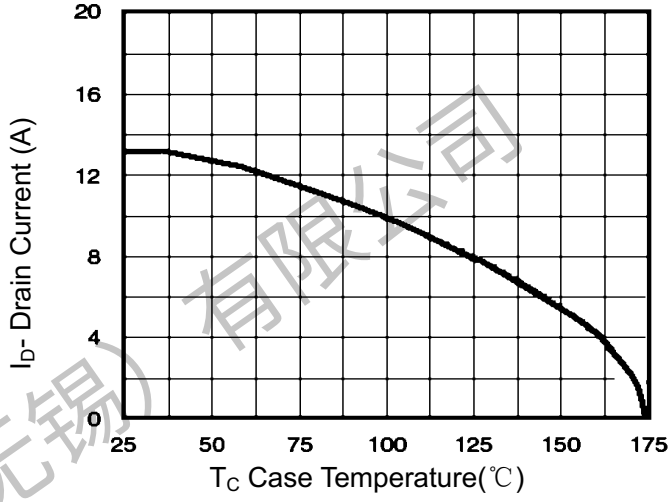


Figure 7 Capacitance vs Vds



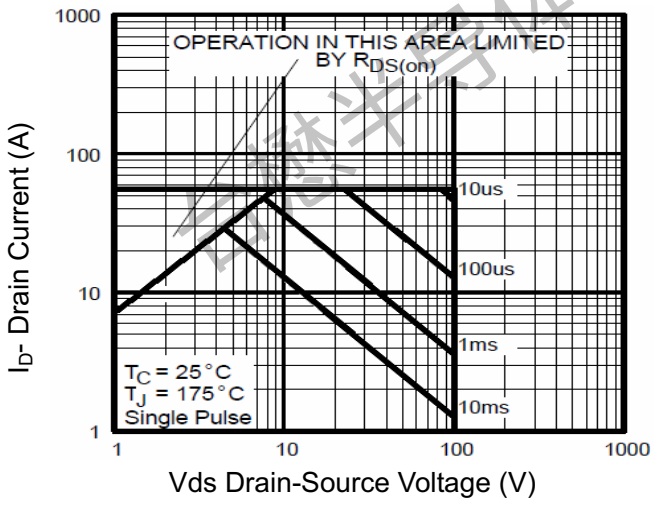


Figure 8 Safe Operation Area

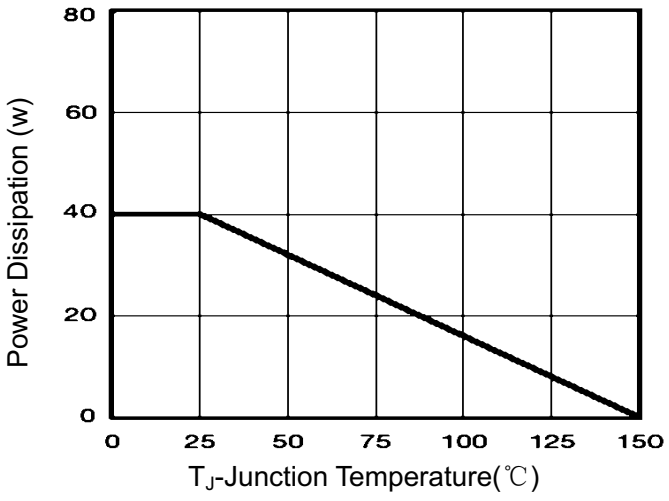


Figure 10 Power De-rating

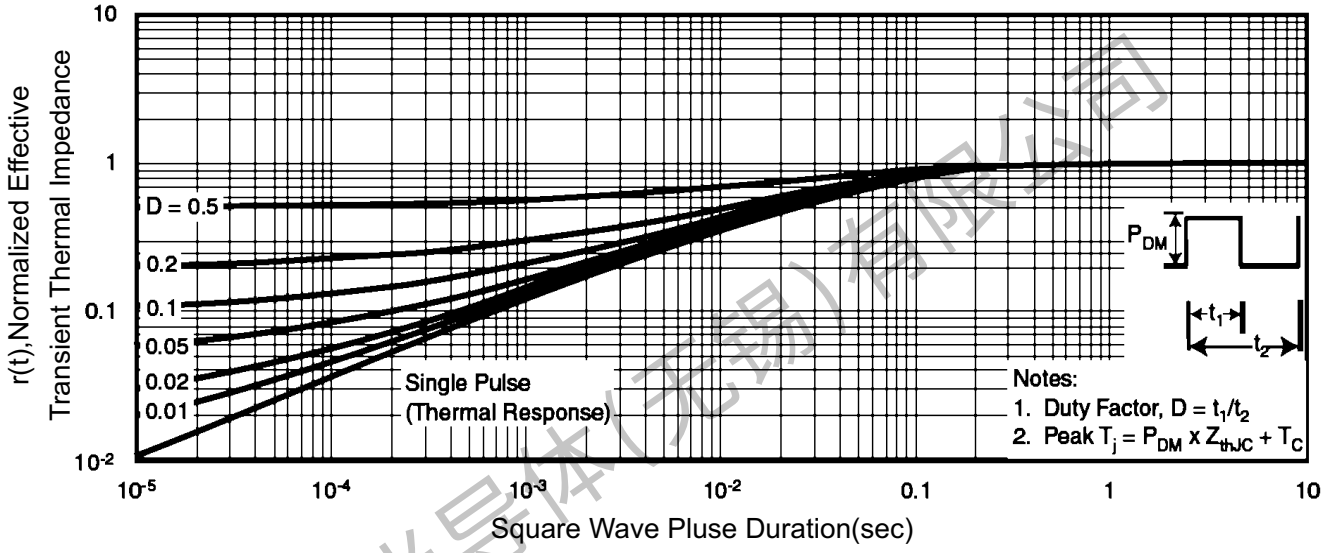
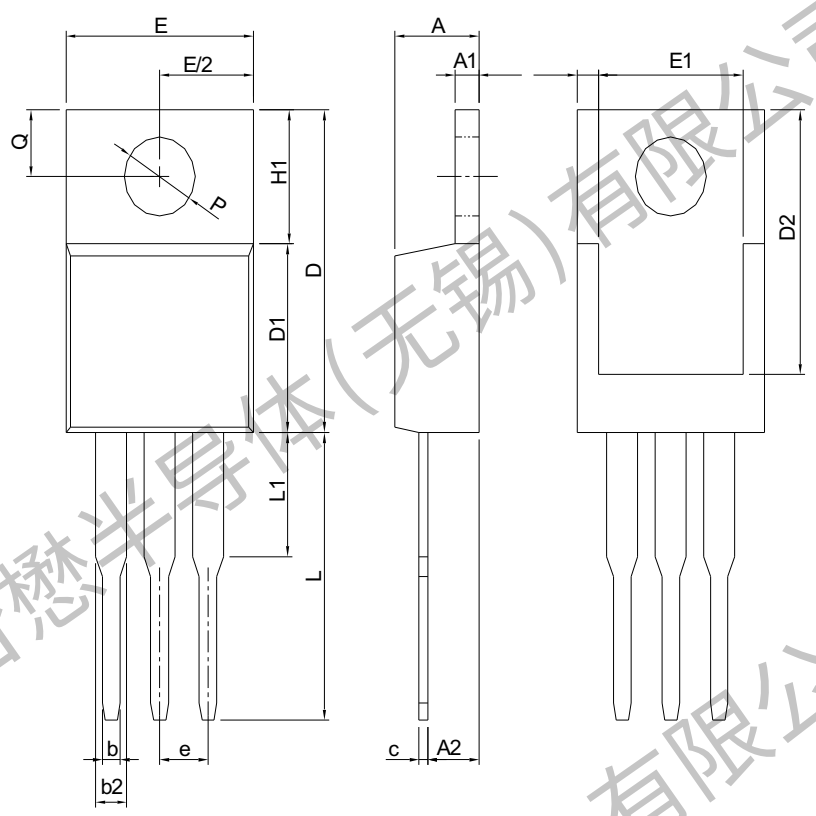


Figure 11 Normalized Maximum Transient Thermal Impedance

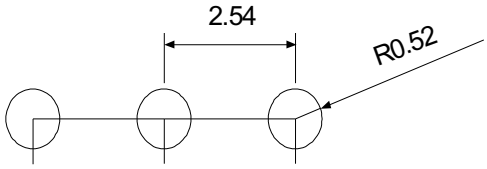
Package Mechanical Data: TO-220AB



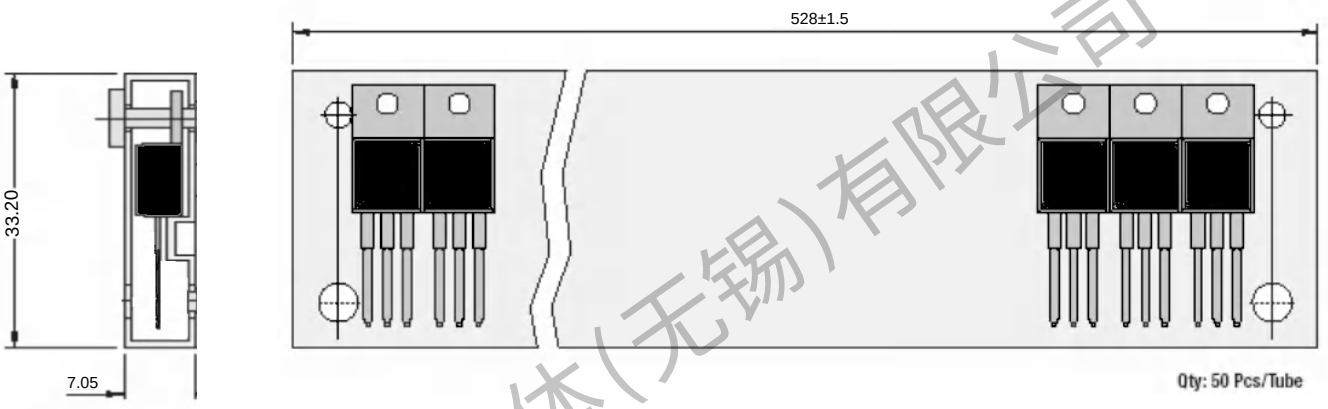
SYMBOL	TO-220			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	3.56	4.83	0.140	0.190
A1	0.51	1.40	0.020	0.055
A2	2.03	2.92	0.080	0.115
b	0.38	1.02	0.015	0.040
b2	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.22	16.51	0.560	0.650
D1	8.38	9.02	0.330	0.355
D2	12.19	13.65	0.480	0.537
E	9.65	10.67	0.380	0.420
E1	6.86	8.89	0.270	0.350
e	2.54 BSC		0.100 BSC	
H1	5.84	6.86	0.230	0.270
L	12.70	14.73	0.500	0.580
L1	-	6.35	-	0.250
P	3.53	4.09	0.139	0.161
Q	2.54	3.43	0.100	0.135

Note: Follow JEDEC TO-220 AB.

RECOMMENDED LAND PATTERN



UNIT: mm

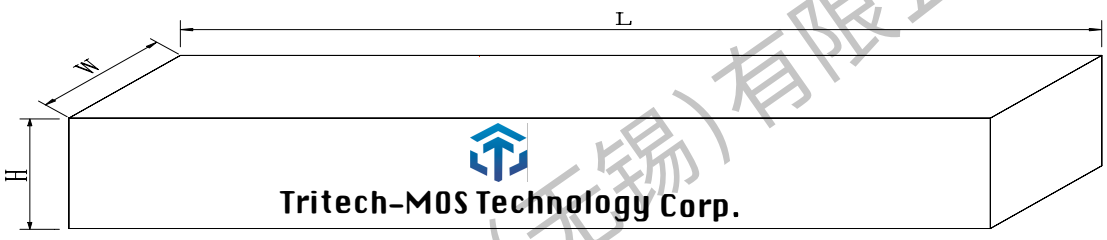


All Dimensions are in mm

1.TO-220AB Packaging

Package	Packing Form	Quantity		
		Tube	Inner Box [kpcs]	Outbox [kpcs]
TO-220AB	Tube Tape	50	5	1

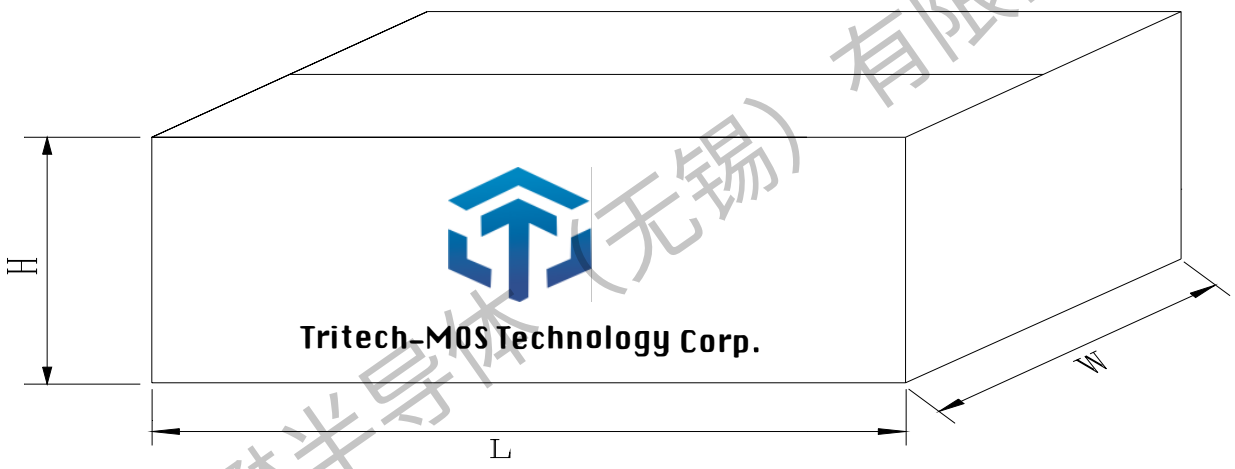
Inner Box



Dimension : 580 (L)×154(W) ×49(H) mm

Quantity : 50 ×20Ea = 1Kpcs

Outer Box



Dimension : 595(L)×285(W) ×185(H) mm

Quantity : 1K×5Ea = 5Kpcs

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Revision history:

Date	Rev	Description	Page
2023.06.30	23.06	Original	